FIG. 1

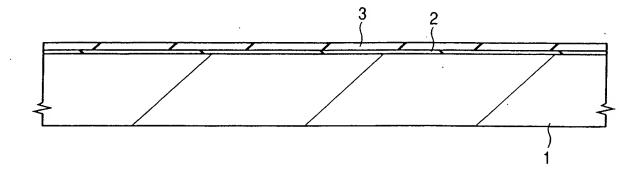


FIG. 2

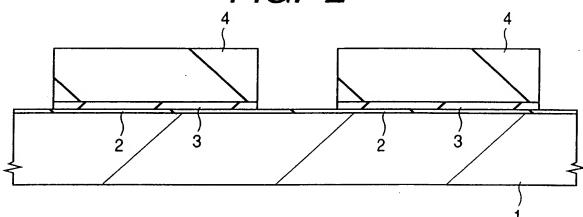
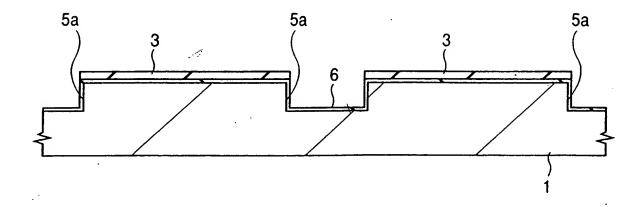


FIG. 3



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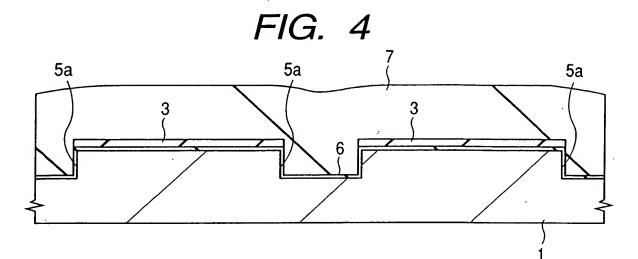


FIG. 5

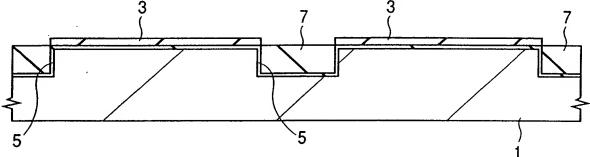


FIG. 6

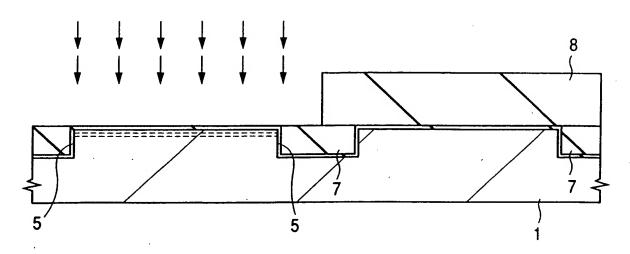


FIG. 7

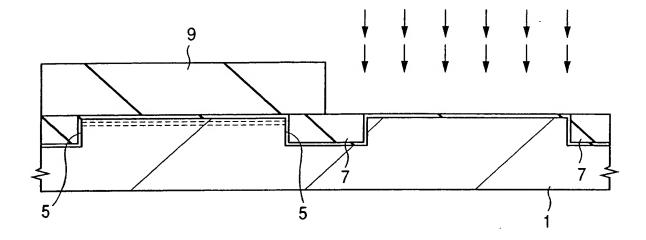


FIG. 8

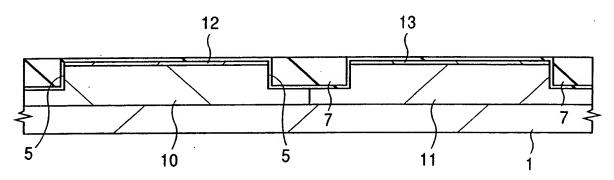
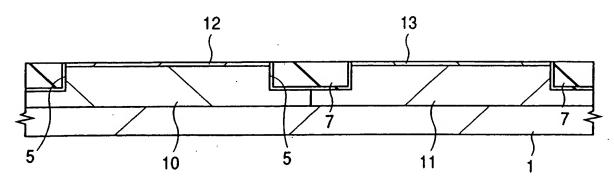


FIG. 10



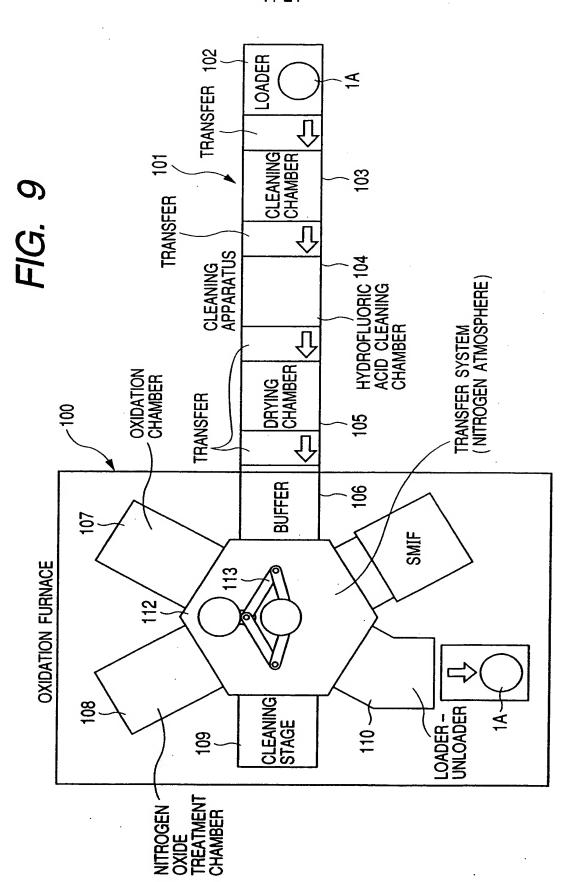
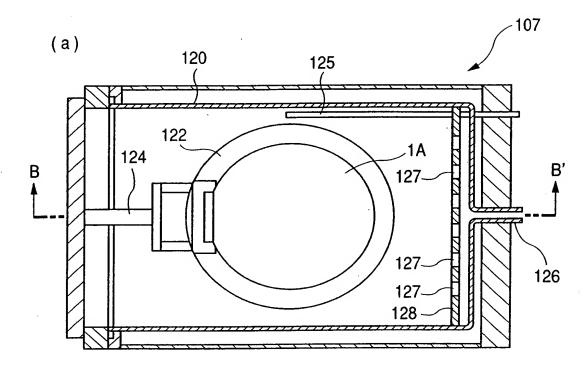


FIG. 11



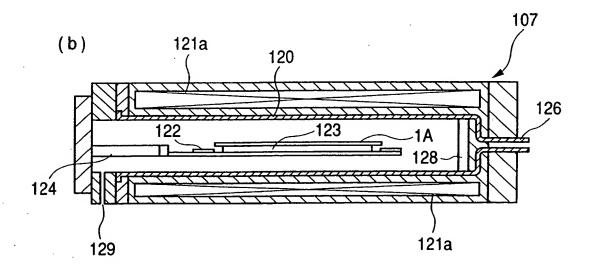
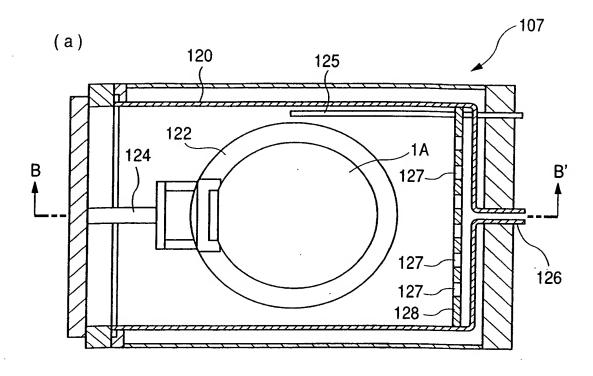
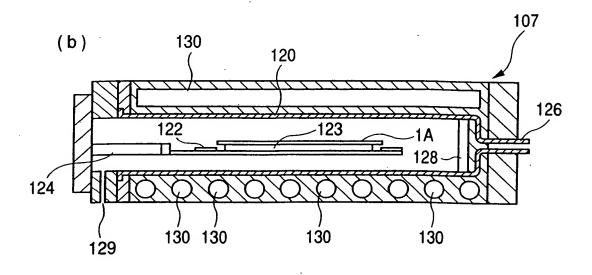
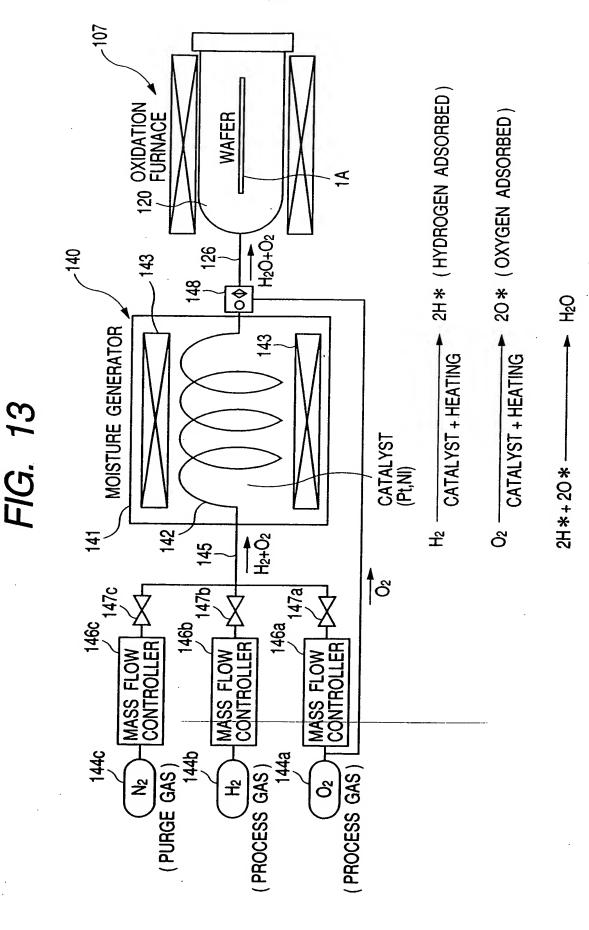
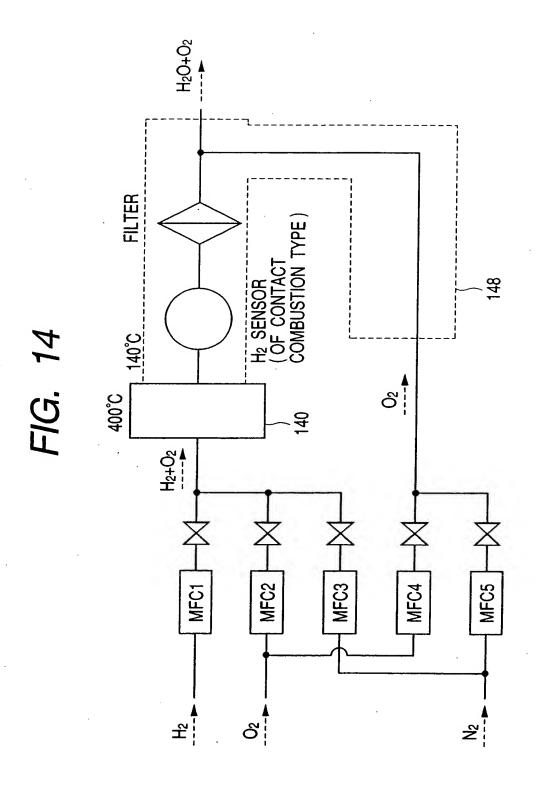


FIG. 12









		TIME	<u></u>	N2 FLOW RATE		O ₂ FLOW RATE			H ₂ FLOW RATE		
FIG. 15	WAFER LOAD	55,,									
	N ₂ PURGE	`									
	O ₂ PURGE	0 – 55"									
	H ₂ INTRODUCTION	15"									
	OXIDATION	ດໃ									
	AFTER- PURGE	2, 20,,									/
	WAFER	55,,					•				

()[]

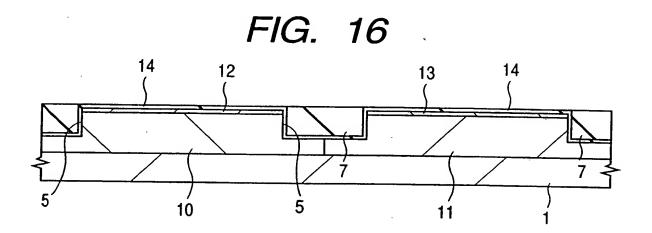


FIG. 17

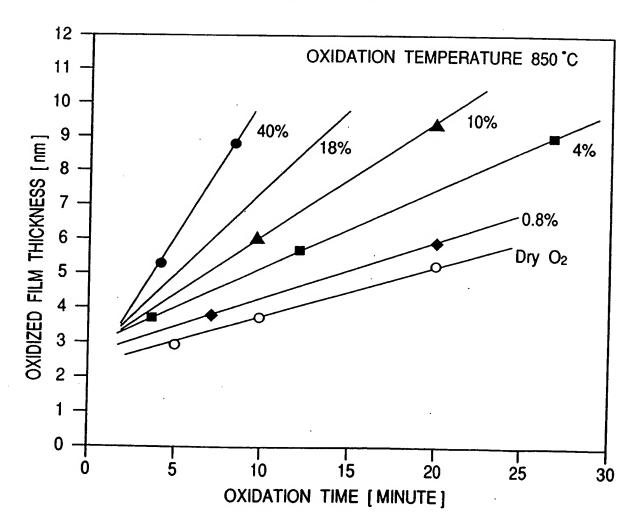
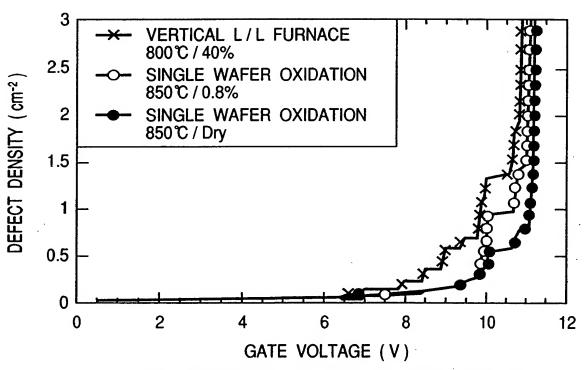


FIG. 18



INITIAL WITHSTAND VOLTAGE OF LOW MOISTURE CONTENT OXIDE FILM (OXIDE FILM THICKNESS = $9nm,S = 0.19cm^2$)

FIG. 19

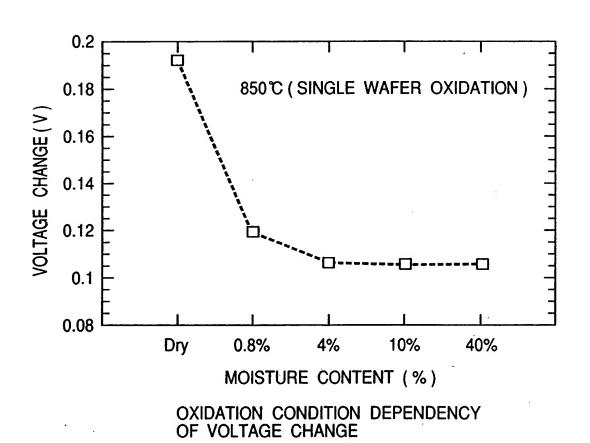
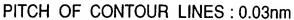
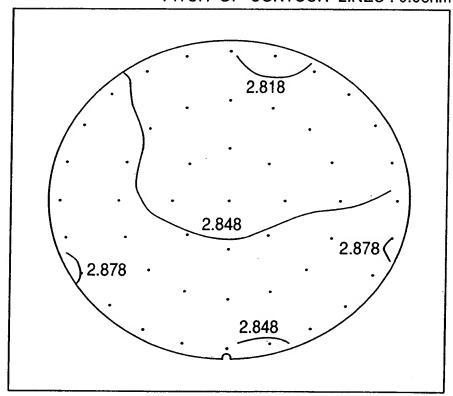


FIG. 20





WAFER DIAMETER: 8 inch

AVERAGE: 2.848 [nm]

MAX.: 2.881 [nm] MIN.: 2.814 [nm]

MAX. – MIN. : 0.067 [nm]

±1.18[%]

TREATING CONDITIONS: 850°C, 2'30"

 H_2/O_2 : 0.05/4.9slm (MOISTURE CONTENT: 0.8%) MEASUREMENT: AT 49 POINTS BY ELLIPSOMETER

FIG. 21

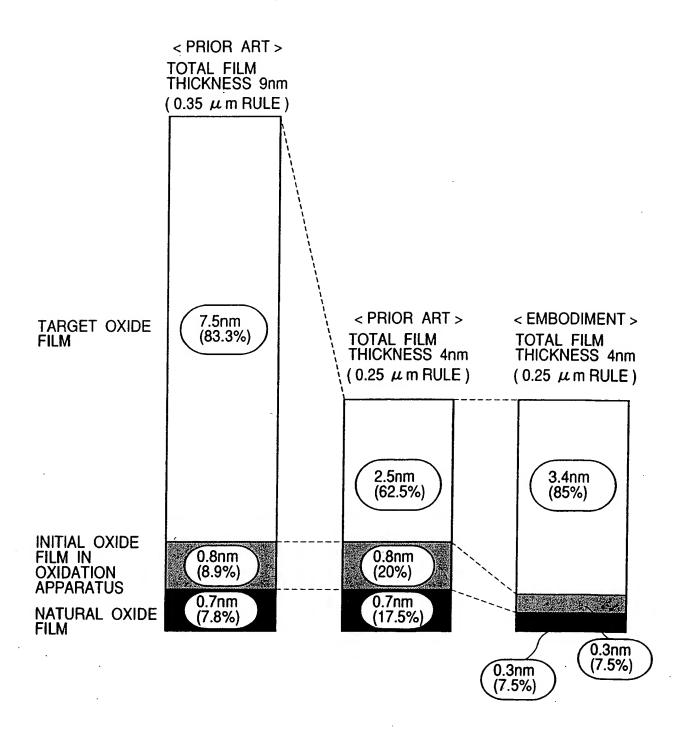
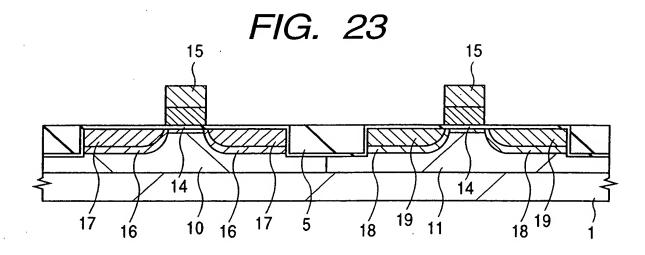


FIG. 22

15
14
14
7
7
11
11
11



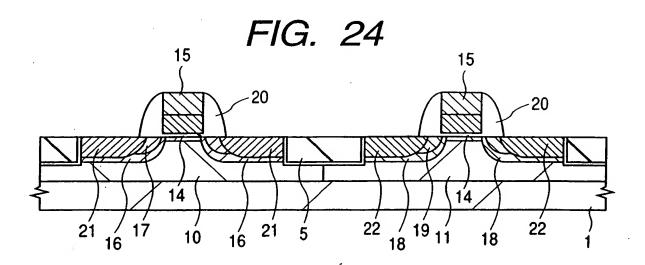


FIG. 25

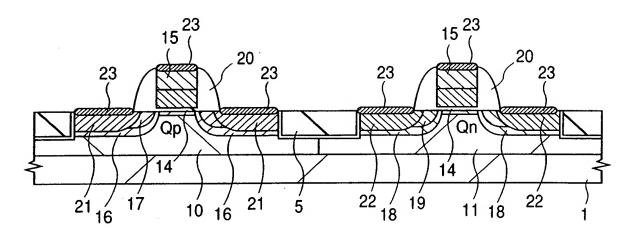


FIG. 26

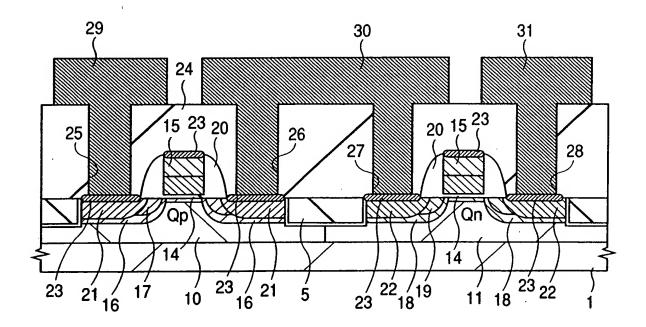


FIG. 27

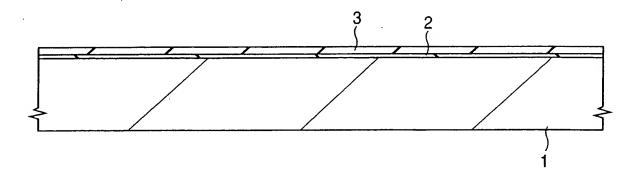


FIG. 28

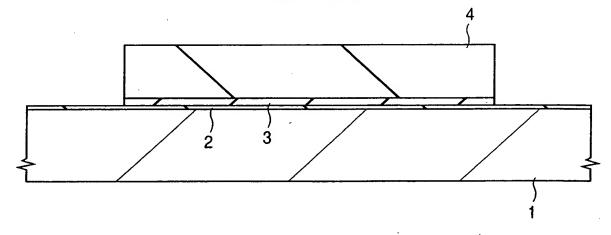
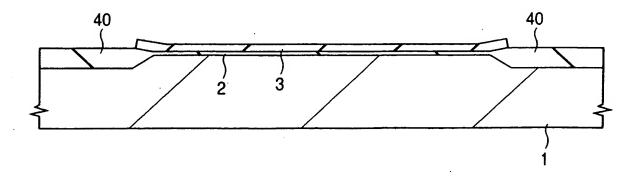
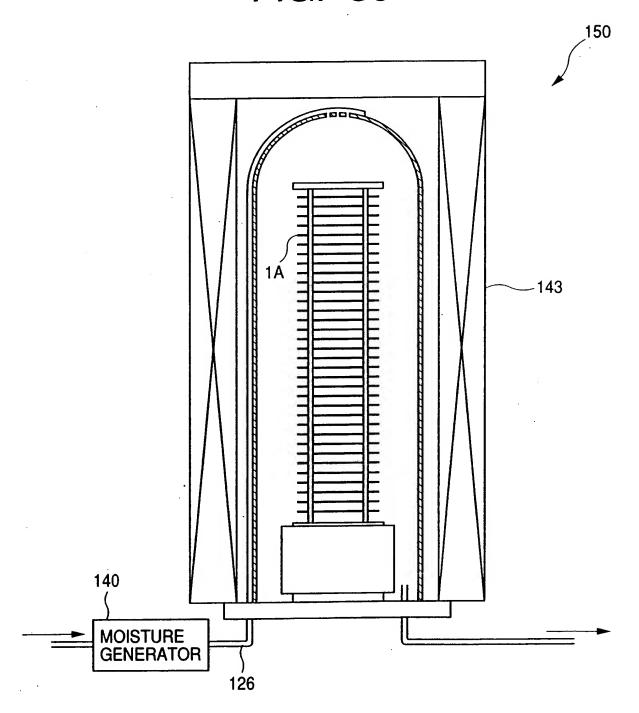


FIG. 29

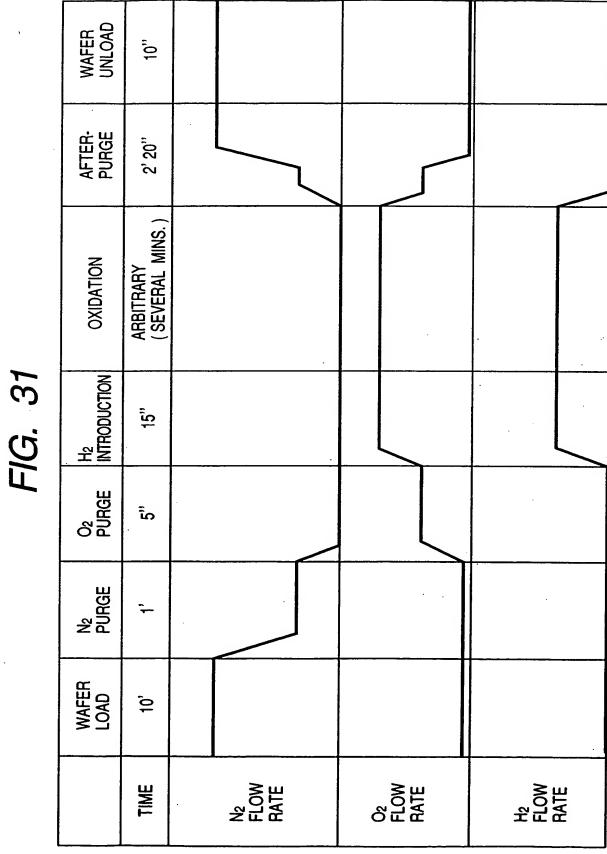


 $(\tilde{})(\tilde{})$

FIG. 30



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FIG. 32

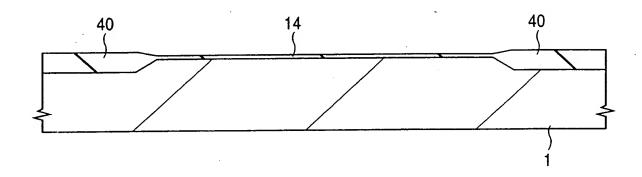
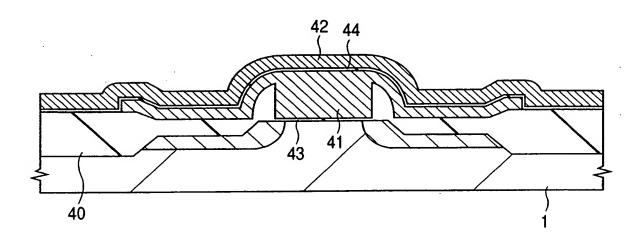


FIG. 34



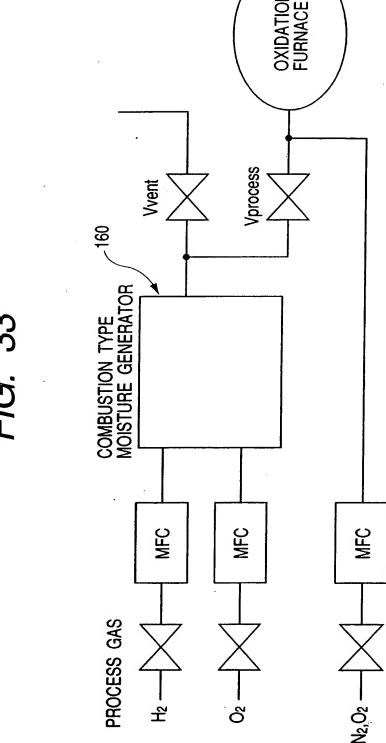


FIG. 33